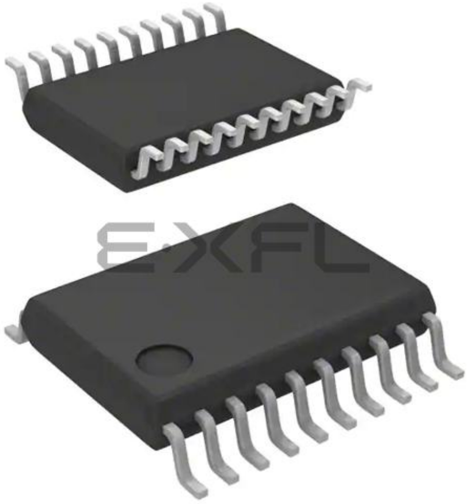
Renesas Electronics America Inc - R5F21294JSP#W4 Datasheet



Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	13
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 4x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21294jsp-w4

Table 1.2 Functions and Specifications for R8C/29 Group

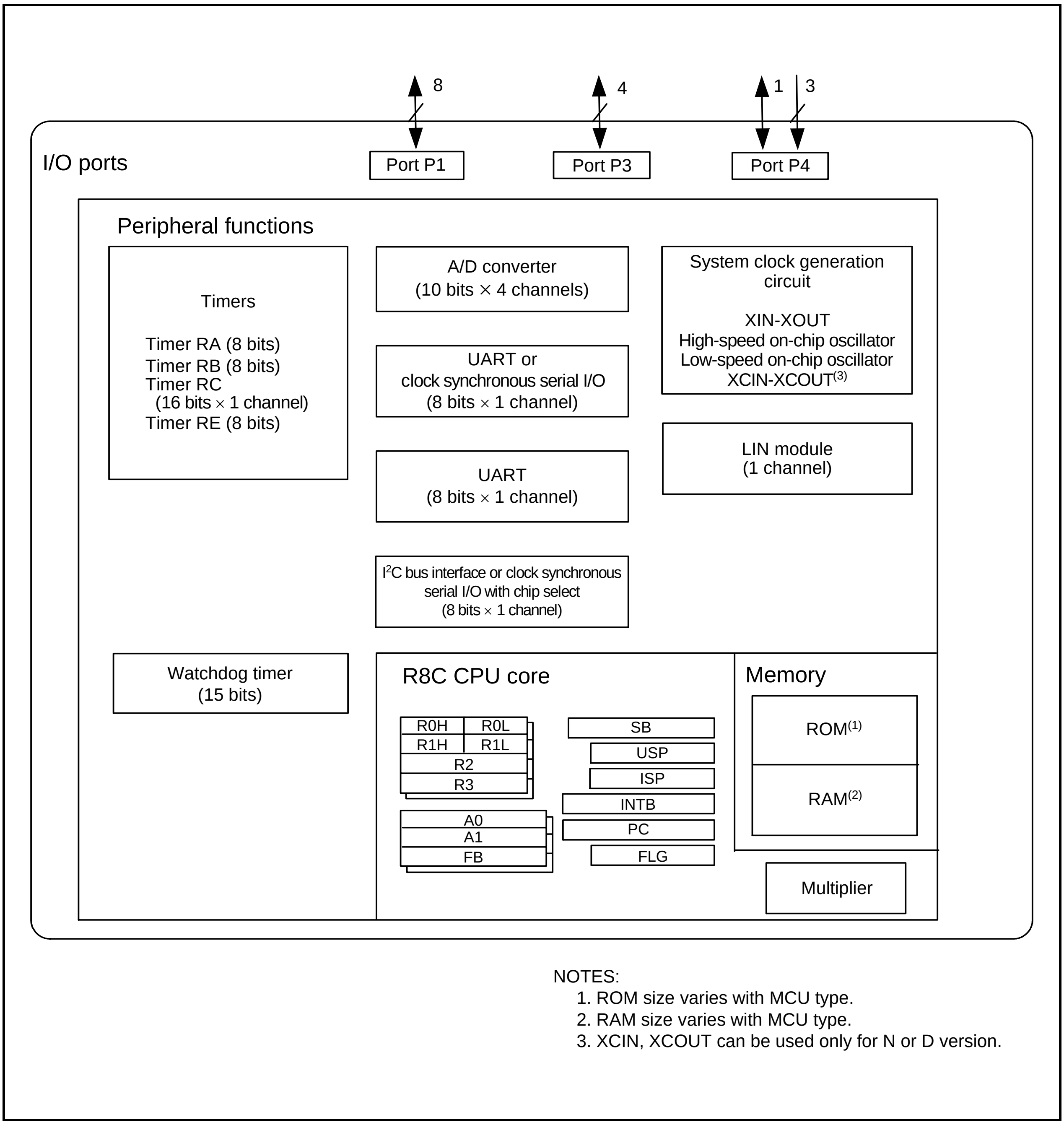
Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) (other than K version) 62.5 ns (f(XIN) = 16 MHz, VCC = 3.0 to 5.5 V) (K version) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V) 200 ns (f(XIN) = 5 MHz, VCC = 2.2 to 5.5 V) (N, D version)
	Operating mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to **Table 1.4 Product Information for R8C/29 Group**
Peripheral Functions	Ports	I/O ports: 13 pins, Input port: 3 pins
	LED drive ports	I/O ports: 8 pins (N, D version)
	Timers	Timer RA: 8 bits × 1 channel Timer RB: 8 bits × 1 channel (Each timer equipped with 8-bit prescaler) Timer RC: 16 bits × 1 channel (Input capture and output compare circuits) Timer RE: With real-time clock and compare match function (For J, K version, compare match function only.)
	Serial interfaces	1 channel (UART0): Clock synchronous serial I/O, UART 1 channel (UART1): UART
	Clock synchronous serial interface	1 channel I^{2}C bus Interface(1) Clock synchronous serial I/O with chip select
	LIN module	Hardware LIN: 1 channel (timer RA, UART0)
	A/D converter	10-bit A/D converter: 1 circuit, 4 channels
	Watchdog timer	15 bits × 1 channel (with prescaler) Reset start selectable
	Interrupts	Internal: 15 sources (N, D version), Internal: 14 sources (J, K version) External: 4 sources, Software: 4 sources, Priority levels: 7 levels
	Clock generation circuits	3 circuits • XIN clock generation circuit (with on-chip feedback resistor) • On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has a frequency adjustment function • XCIN clock generation circuit (32 kHz) (N, D version) • Real-time clock (timer RE) (N, D version)
	Oscillation stop detection function	XIN clock oscillation stop detection function
	Voltage detection circuit	On-chip
	Power-on reset circuit	On-chip
Electrical Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz) (other than K version) VCC = 3.0 to 5.5 V (f(XIN) = 16 MHz) (K version) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz) VCC = 2.2 to 5.5 V (f(XIN) = 5 MHz) (N, D version)
	Current consumption (N, D version)	Typ. 10 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 6 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 2.0 μA (VCC = 3.0 V, wait mode (f(XCIN) = 32 kHz) Typ. 0.7 μA (VCC = 3.0 V, stop mode)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	10,000 times (data flash)
		1,000 times (program ROM)
Operating Ambient Temperature		-20 to 85°C (N version)
		-40 to 85°C (D, J version)(2), -40 to 125°C (K version)(2)
Package		20-pin molded-plastic LSSOP

NOTES:

1. I^{2}C bus is a trademark of Koninklijke Philips Electronics N. V.
2. Specify the D, K version if D, K version functions are to be used.

1.3 Block Diagram

Figure 1.1 shows a Block Diagram.



NOTES:
1. ROM size varies with MCU type.
2. RAM size varies with MCU type.
3. XCIN, XCOUT can be used only for N or D version.

Figure 1.1 Block Diagram

1.4 Product Information

Table 1.3 lists the Product Information for R8C/28 Group and Table 1.4 lists the Product Information for R8C/29 Group.

Table 1.3 Product Information for R8C/28 Group **Current of Sep. 2008**

Type No.	ROM Capacity	RAM Capacity	Package Type	Remarks	
R5F21282SNSP	8 Kbytes	512 bytes	PLSP0020JB-A	N version	
R5F21284SNSP	16 Kbytes	1 Kbyte	PLSP0020JB-A		
R5F21282SDSP	8 Kbytes	512 bytes	PLSP0020JB-A	D version	
R5F21284SDSP	16 Kbytes	1 Kbyte	PLSP0020JB-A		
R5F21284JSP	16 Kbytes	1 Kbyte	PLSP0020JB-A	J version	
R5F21286JSP	32 Kbytes	1.5 Kbyte	PLSP0020JB-A		
R5F21284KSP	16 Kbytes	1 Kbyte	PLSP0020JB-A	K version	
R5F21286KSP	32 Kbytes	1.5 Kbyte	PLSP0020JB-A		
R5F21282SNXXXSP	8 Kbytes	512 bytes	PLSP0020JB-A	N version	Factory programming product(1)
R5F21284SNXXXSP	16 Kbytes	1 Kbyte	PLSP0020JB-A		
R5F21282SDXXXSP	8 Kbytes	512 bytes	PLSP0020JB-A	D version	
R5F21284SDXXXSP	16 Kbytes	1 Kbyte	PLSP0020JB-A		
R5F21284JXXXSP	16 Kbytes	1 Kbyte	PLSP0020JB-A	J version	
R5F21286JXXXSP	32 Kbytes	1.5 Kbyte	PLSP0020JB-A		
R5F21284KXXXSP	16 Kbytes	1 Kbyte	PLSP0020JB-A	K version	
R5F21286KXXXSP	32 Kbytes	1.5 Kbyte	PLSP0020JB-A		

NOTE:
1. The user ROM is programmed before shipment.

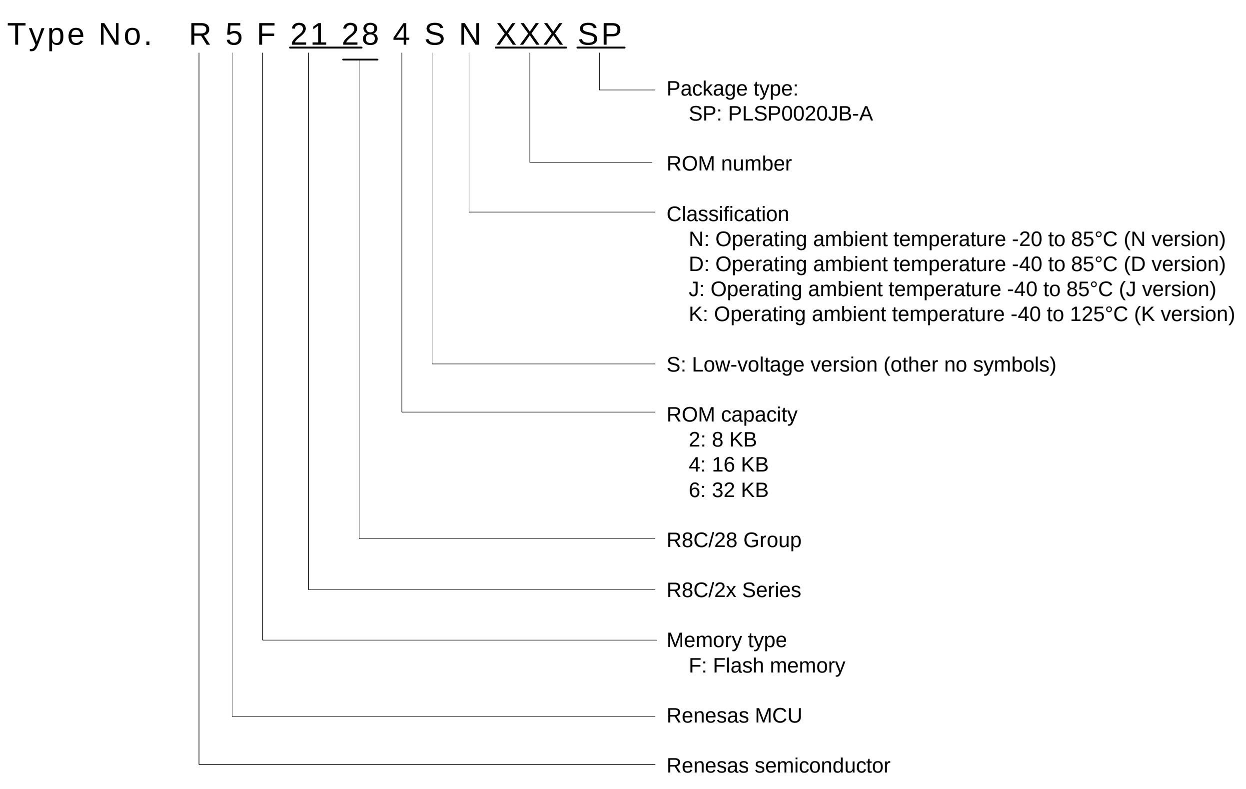


Figure 1.2 Type Number, Memory Size, and Package of R8C/28 Group

Table 1.4 Product Information for R8C/29 Group **Current of Sep. 2008**

Type No.	ROM Capacity		RAM Capacity	Package Type	Remarks	
	Program ROM	Data flash				
R5F21292SNSP	8 Kbytes	1 Kbyte × 2	512 bytes	PLSP0020JB-A	N version	
R5F21294SNSP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLSP0020JB-A		
R5F21292SDSP	8 Kbytes	1 Kbyte × 2	512 bytes	PLSP0020JB-A	D version	
R5F21294SDSP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLSP0020JB-A		
R5F21294JSP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLSP0020JB-A	J version	
R5F21296JSP	32 Kbytes	1 Kbyte × 2	1.5 Kbyte	PLSP0020JB-A		
R5F21294KSP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLSP0020JB-A	K version	
R5F21296KSP	32 Kbytes	1 Kbyte × 2	1.5 Kbyte	PLSP0020JB-A		
R5F21292SNXXXSP	8 Kbytes	1 Kbyte × 2	512 bytes	PLSP0020JB-A	N version	Factory programming product(1)
R5F21294SNXXXSP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLSP0020JB-A		
R5F21292SDXXXSP	8 Kbytes	1 Kbyte × 2	512 bytes	PLSP0020JB-A	D version	
R5F21294SDXXXSP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLSP0020JB-A		
R5F21294JXXXSP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLSP0020JB-A	J version	
R5F21296JXXXSP	32 Kbytes	1 Kbyte × 2	1.5 Kbyte	PLSP0020JB-A		
R5F21294KXXXSP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLSP0020JB-A	K version	
R5F21296KXXXSP	32 Kbytes	1 Kbyte × 2	1.5 Kbyte	PLSP0020JB-A		

NOTE:

1. The user ROM is programmed before shipment.

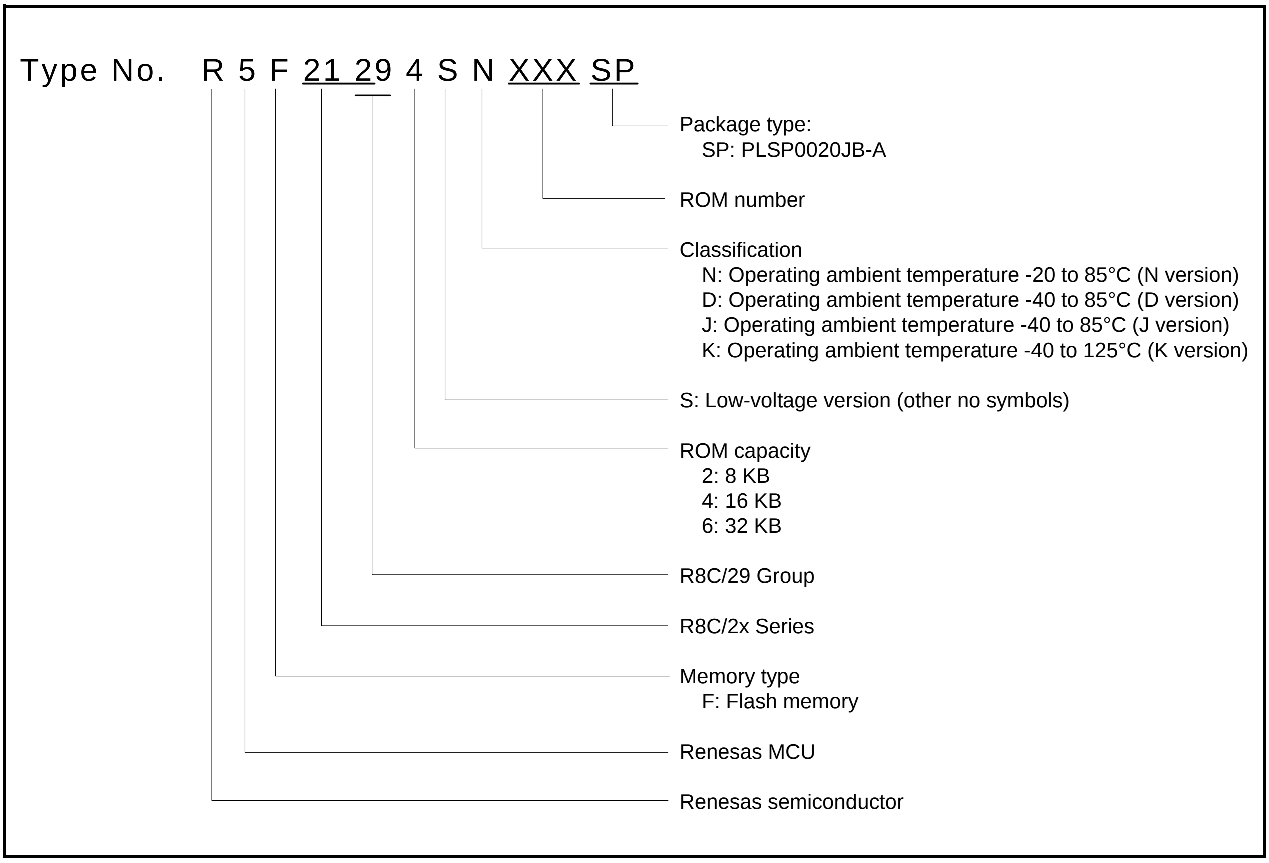


Figure 1.3 Type Number, Memory Size, and Package of R8C/29 Group

1.6 Pin Functions

Table 1.5 lists Pin Functions.

Table 1.5 Pin Functions

Type	Symbol	I/O Type	Description
Power supply input	VCC, VSS	I	Apply 2.2 to 5.5 V (J, K version are 2.7 to 5.5 V) to the VCC pin. Apply 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS	I	Power supply for the A/D converter. Connect a capacitor between AVCC and AVSS.
Reset input	$\overline{\text{RESET}}$	I	Input “L” on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
XIN clock input	XIN	I	These pins are provided for XIN clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins. To use an external clock, input it to the XIN pin and leave the XOUT pin open.
XIN clock output	XOUT	O	
XCIN clock input (N, D version)	XCIN	I	These pins are provided for XCIN clock generation circuit I/O. Connect a crystal oscillator between the XCIN and XCOUT pins. To use an external clock, input it to the XCIN pin and leave the XCOUT pin open.
XCIN clock output (N, D version)	XCOUT	O	
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT3}}$	I	$\overline{\text{INT}}$ interrupt input pins
Key input interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins
Timer RA	TRAO	O	Timer RA output pin
	TRAIO	I/O	Timer RA I/O pin
Timer RB	TRBO	O	Timer RB output pin
Timer RC	TRCCLK	I	External clock input pin
	TRCTRG	I	External trigger input pin
	TRCIOA, TRCIOB, TRCIOC, TRCIOD	I/O	Sharing output-compare output / input-capture input / PWM / PWM2 output pins
Serial interface	CLK0	I/O	Clock I/O pin
	RXD0, RXD1	I	Receive data input pin
	TXD0, TXD1	O	Transmit data output pin
I^{2}C bus interface	SCL	I/O	Clock I/O pin
	SDA	I/O	Data I/O pin
Clock synchronous serial I/O with chip select	SSI	I/O	Data I/O pin
	$\overline{\text{SCS}}$	I/O	Chip-select signal I/O pin
	SSCK	I/O	Clock I/O pin
	SSO	I/O	Data I/O pin
Reference voltage input	VREF	I	Reference voltage input pin to A/D converter
A/D converter	AN8 to AN11	I	Analog input pins to A/D converter
I/O port	P1_0 to P1_7, P3_3 to P3_5, P3_7, P4_5	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. P1_0 to P1_7 also function as LED drive ports (N, D version).
Input port	P4_2, P4_6, P4_7	I	Input-only ports

I: Input O: Output I/O: Input and output

2.1 Data Registers (R0, R1, R2, and R3)

R0 is a 16-bit register for transfer, arithmetic, and logic operations. The same applies to R1 to R3. R0 can be split into high-order bits (R0H) and low-order bits (R0L) to be used separately as 8-bit data registers. R1H and R1L are analogous to R0H and R0L. R2 can be combined with R0 and used as a 32-bit data register (R2R0). R3R1 is analogous to R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. It is also used for transfer, arithmetic, and logic operations. A1 is analogous to A0. A1 can be combined with A0 and as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the start address of an interrupt vector table.

2.5 Program Counter (PC)

PC is 20 bits wide and indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointers (SP), USP, and ISP, are each 16 bits wide. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register indicating the CPU state.

2.8.1 Carry Flag (C)

The C flag retains carry, borrow, or shift-out bits that have been generated by the arithmetic and logic unit.

2.8.2 Debug Flag (D)

The D flag is for debugging only. Set it to 0.

2.8.3 Zero Flag (Z)

The Z flag is set to 1 when an arithmetic operation results in 0; otherwise to 0.

2.8.4 Sign Flag (S)

The S flag is set to 1 when an arithmetic operation results in a negative value; otherwise to 0.

2.8.5 Register Bank Select Flag (B)

Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is set to 1.

2.8.6 Overflow Flag (O)

The O flag is set to 1 when an operation results in an overflow; otherwise to 0.

3.2 R8C/29 Group

Figure 3.2 is a Memory Map of R8C/29 Group. The R8C/29 group has 1 Mbyte of address space from addresses 00000h to FFFFFh.

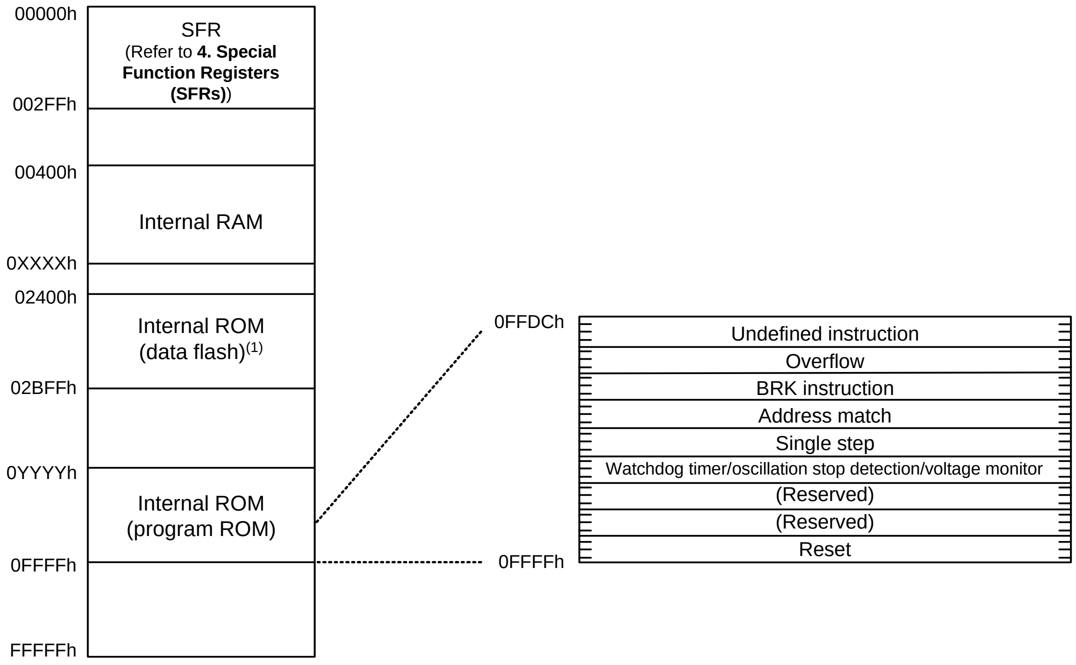
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.

The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.

The internal RAM area is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F21292SNSP, R5F21292SDSP, R5F21292SNXXXSP, R5F21292SDXXXSP	8 Kbytes	0E000h	512 bytes	005FFh
R5F21294SNSP, R5F21294SDSP, R5F21294JSP, R5F21294KSP, R5F21294SNXXXSP, R5F21294SDXXXSP, R5F21294JXXXSP, R5F21294KXXXSP	16 Kbytes	0C000h	1 Kbyte	007FFh
R5F21296JSP, R5F21296KSP, R5F21296JXXXSP, R5F21296KXXXSP	32 Kbytes	08000h	1.5 Kbytes	009FFh

Figure 3.2 Memory Map of R8C/29 Group

5. Electrical Characteristics

5.1 N, D Version

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}/AV_{CC}	Supply voltage		-0.3 to 6.5	V
V_I	Input voltage		-0.3 to V_{CC} + 0.3	V
V_O	Output voltage		-0.3 to V_{CC} + 0.3	V
P_d	Power dissipation	T_{opr} = 25°C	500	mW
T_{opr}	Operating ambient temperature		-20 to 85 (N version) / -40 to 85 (D version)	°C
T_{stg}	Storage temperature		-65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage			2.2	–	5.5	V
V_{SS}/AV_{SS}	Supply voltage			–	0	–	V
V_{IH}	Input “H” voltage			0.8 V_{CC}	–	V_{CC}	V
V_{IL}	Input “L” voltage			0	–	0.2 V_{CC}	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$		–	–	-160	mA
$I_{OH(sum)}$	Average sum output “H” current	Sum of all pins $I_{OH(avg)}$		–	–	-80	mA
$I_{OH(peak)}$	Peak output “H” current	Except P1_0 to P1_7		–	–	-10	mA
		P1_0 to P1_7		–	–	-40	mA
$I_{OH(avg)}$	Average output “H” current	Except P1_0 to P1_7		–	–	-5	mA
		P1_0 to P1_7		–	–	-20	mA
$I_{OL(sum)}$	Peak sum output “L” currents	Sum of all pins $I_{OL(peak)}$		–	–	160	mA
$I_{OL(sum)}$	Average sum output “L” currents	Sum of all pins $I_{OL(avg)}$		–	–	80	mA
$I_{OL(peak)}$	Peak output “L” currents	Except P1_0 to P1_7		–	–	10	mA
		P1_0 to P1_7		–	–	40	mA
$I_{OL(avg)}$	Average output “L” current	Except P1_0 to P1_7		–	–	5	mA
		P1_0 to P1_7		–	–	20	mA
$f_{(XIN)}$	XIN clock input oscillation frequency		3.0 V $\le V_{CC} \le$ 5.5 V	0	–	20	MHz
			2.7 V $\le V_{CC} <$ 3.0 V	0	–	10	MHz
			2.2 V $\le V_{CC} <$ 2.7 V	0	–	5	MHz
$f_{(XCIN)}$	XCIN clock input oscillation frequency		2.2 V $\le V_{CC} \le$ 5.5 V	0	–	70	kHz
–	System clock	OCD2 = 0 XIN clock selected	3.0 V $\le V_{CC} \le$ 5.5 V	0	–	20	MHz
			2.7 V $\le V_{CC} <$ 3.0 V	0	–	10	MHz
			2.2 V $\le V_{CC} <$ 2.7 V	0	–	5	MHz
		OCD2 = 1 On-chip oscillator clock selected	FRA01 = 0 Low-speed on-chip oscillator clock selected	–	125	–	kHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 3.0 V $\le V_{CC} \le$ 5.5 V	–	–	20	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 2.7 V $\le V_{CC} \le$ 5.5 V	–	–	10	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 2.2 V $\le V_{CC} \le$ 5.5 V	–	–	5	MHz

NOTES:

1. V_{CC} = 2.2 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.

Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics[4]

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance[2]		10,000[3]	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97 + CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		-20[8]	–	85	°C
–	Data hold time[9]	Ambient temperature = 55°C	20	–	–	year

NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. -40°C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.13 Timing Requirements of Clock Synchronous Serial I/O with Chip Select(1)

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
t_{SUCYC}	SSCK clock cycle time			4	–	–	t_{CYC}(2)
t_{HI}	SSCK clock “H” width			0.4	–	0.6	t_{SUCYC}
t_{LO}	SSCK clock “L” width			0.4	–	0.6	t_{SUCYC}
t_{RISE}	SSCK clock rising time	Master		–	–	1	t_{CYC}(2)
		Slave		–	–	1	µs
t_{FALL}	SSCK clock falling time	Master		–	–	1	t_{CYC}(2)
		Slave		–	–	1	µs
t_{SU}	SSO, SSI data input setup time			100	–	–	ns
t_H	SSO, SSI data input hold time			1	–	–	t_{CYC}(2)
t_{LEAD}	$\overline{SCS}$ setup time	Slave		$1t_{CYC} + 50$	–	–	ns
t_{LAG}	$\overline{SCS}$ hold time	Slave		$1t_{CYC} + 50$	–	–	ns
t_{OD}	SSO, SSI data output delay time			–	–	1	t_{CYC}(2)
t_{SA}	SSI slave access time		$2.7\ V \le V_{CC} \le 5.5\ V$	–	–	$1.5t_{CYC} + 100$	ns
			$2.2\ V \le V_{CC} < 2.7\ V$	–	–	$1.5t_{CYC} + 200$	ns
t_{OR}	SSI slave out open time		$2.7\ V \le V_{CC} \le 5.5\ V$	–	–	$1.5t_{CYC} + 100$	ns
			$2.2\ V \le V_{CC} < 2.7\ V$	–	–	$1.5t_{CYC} + 200$	ns

NOTES:

1. V_{CC} = 2.2 to 5.5 V, V_{SS} = 0 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. $1t_{CYC}$ = 1/f1(s)

Table 5.15 Electrical Characteristics (1) [V_{CC} = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P1_0 to P1_7, XOUT	I_{OH} = -5 mA		V_{CC} - 2.0	–	V_{CC}	V
			I_{OH} = -200 µA		V_{CC} - 0.5	–	V_{CC}	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OH} = -20 mA	V_{CC} - 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -5 mA	V_{CC} - 2.0	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -1 mA	V_{CC} - 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -500 µA	V_{CC} - 2.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except P1_0 to P1_7, XOUT	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 µA		–	–	0.45	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OL} = 20 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 5 mA	–	–	2.0	V
		XOUT	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 µA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, KI0, KI1, KI2, KI3, TRAIO, RXD0, RXD1, CLK0, SSI, SCL, SDA, SSO			0.1	0.5	–	V
		$\overline{RESET}$			0.1	1.0	–	V
I_{IH}	Input “H” current		VI = 5 V, V_{CC} = 5V		–	–	5.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 5V		–	–	-5.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 5V		30	50	167	kΩ
R_{fXIN}	Feedback resistance	XIN			–	1.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	18	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:

1. V_{CC} = 4.2 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.16 Electrical Characteristics (2) [Vcc = 5 V]
(T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current (V_{CC} = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are V_{SS}	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	10	17	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	9	15	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6	–	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	5	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	10	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5.5	10	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	130	300	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	130	300	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	30	–	µA

Table 5.26 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLK0 input cycle time	300	–	ns
$t_{W(CKH)}$	CLK0 input “H” width	150	–	ns
$t_{W(CKL)}$	CLK0 Input “L” width	150	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	80	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	70	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 or 1

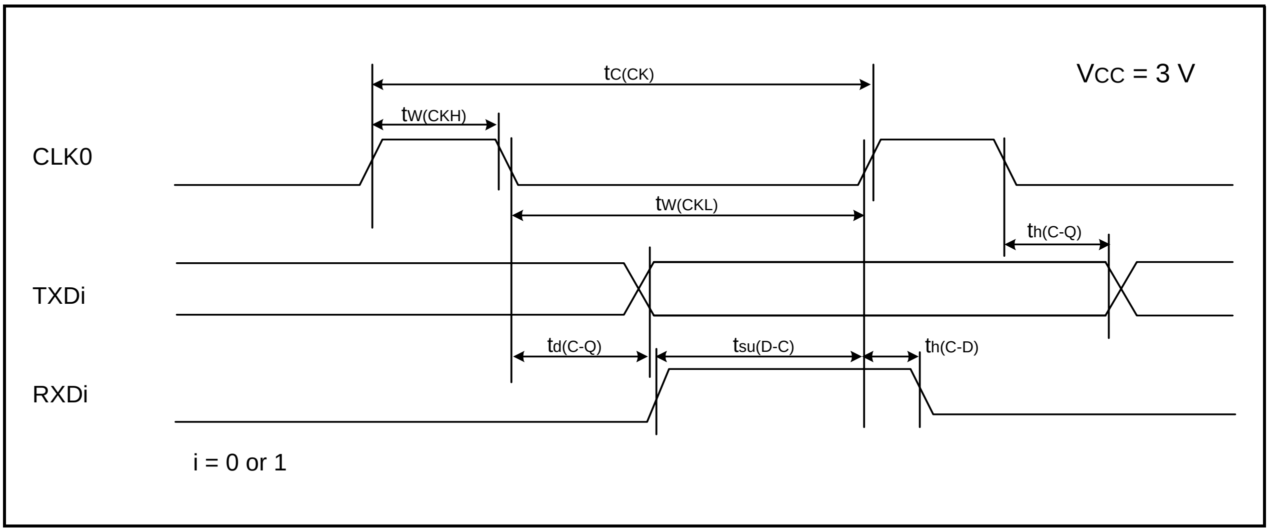


Figure 5.14 Serial Interface Timing Diagram when V_{CC} = 3 V

Table 5.27 External Interrupt $\overline{\text{INTi}}$ (i = 0, 1, 3) Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{\text{INTi}}$ input “H” width	380(1)	–	ns
$t_{W(INL)}$	$\overline{\text{INTi}}$ input “L” width	380(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{\text{INTi}}$ input filter select bit, use an $\overline{\text{INTi}}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{\text{INTi}}$ input filter select bit, use an $\overline{\text{INTi}}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

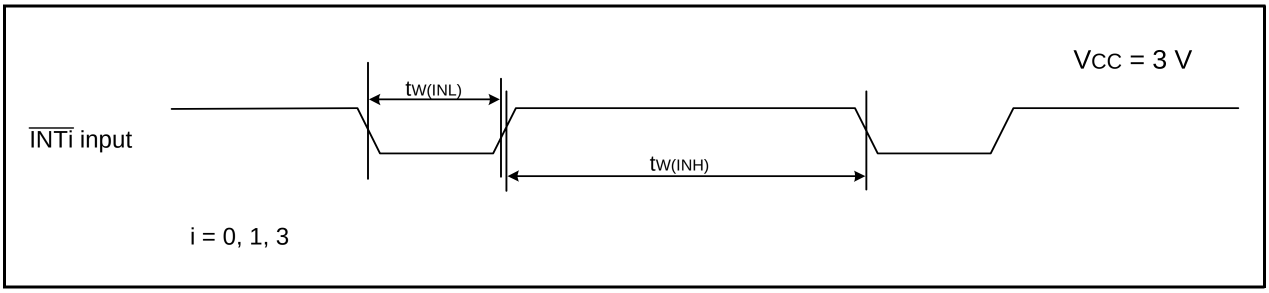


Figure 5.15 External Interrupt $\overline{\text{INTi}}$ Input Timing Diagram when V_{CC} = 3 V

5.2 J, K Version

Table 5.34 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}/AV_{CC}	Supply voltage		-0.3 to 6.5	V
V_I	Input voltage		-0.3 to V_{CC} + 0.3	V
V_O	Output voltage		-0.3 to V_{CC} + 0.3	V
P_d	Power dissipation	-40 °C ≤ T_{opr} ≤ 85 °C	300	mW
		85 °C ≤ T_{opr} ≤ 125 °C	125	mW
T_{opr}	Operating ambient temperature		-40 to 85 (J version) / -40 to 125 (K version)	°C
T_{stg}	Storage temperature		-65 to 150	°C

Table 5.35 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage			2.7	–	5.5	V
V_{SS}/AV_{SS}	Supply voltage			–	0	–	V
V_{IH}	Input “H” voltage			0.8 V_{CC}	–	V_{CC}	V
V_{IL}	Input “L” voltage			0	–	0.2 V_{CC}	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$		–	–	-60	mA
$I_{OH(peak)}$	Peak output “H” current			–	–	-10	mA
$I_{OH(avg)}$	Average output “H” current			–	–	-5	mA
$I_{OL(sum)}$	Peak sum output “L” currents	Sum of all pins $I_{OL(peak)}$		–	–	60	mA
$I_{OL(peak)}$	Peak output “L” currents			–	–	10	mA
$I_{OL(avg)}$	Average output “L” current			–	–	5	mA
$f_{(XIN)}$	XIN clock input oscillation frequency		3.0 V ≤ V_{CC} ≤ 5.5 V (other than K version)	0	–	20	MHz
			3.0 V ≤ V_{CC} ≤ 5.5 V (K version)	0	–	16	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
–	System clock	OCD2 = 0 XIN clock selected	3.0 V ≤ V_{CC} ≤ 5.5 V (other than K version)	0	–	20	MHz
			3.0 V ≤ V_{CC} ≤ 5.5 V (K version)	0	–	16	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
		OCD2 = 1 On-chip oscillator clock selected	FRA01 = 0 Low-speed on-chip oscillator clock selected	–	125	–	kHz
			FRA01 = 1 High-speed on-chip oscillator clock selected (other than K version)	–	–	20	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected	–	–	10	MHz

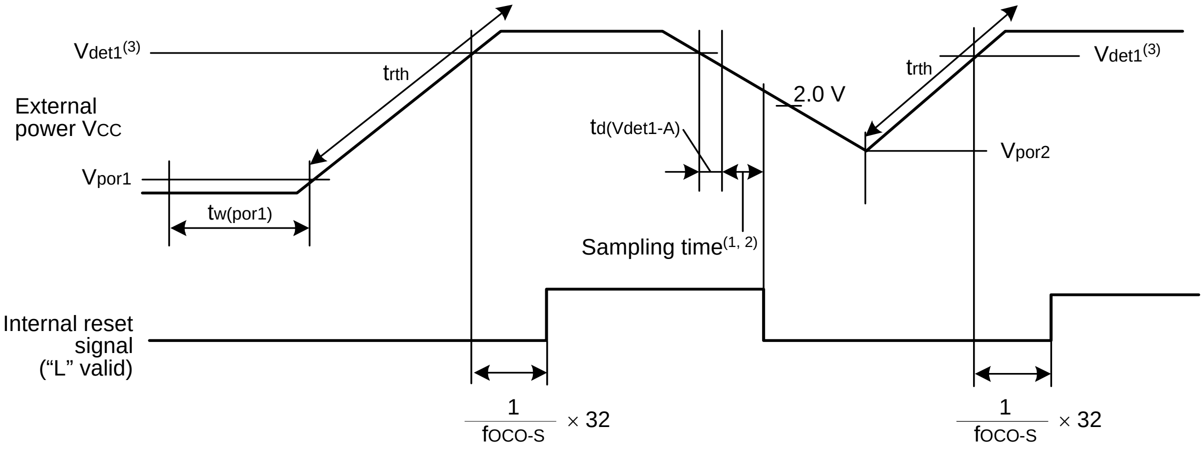
NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.

Table 5.41 Power-on Reset Circuit, Voltage Monitor 1 Reset Electrical Characteristics(3)

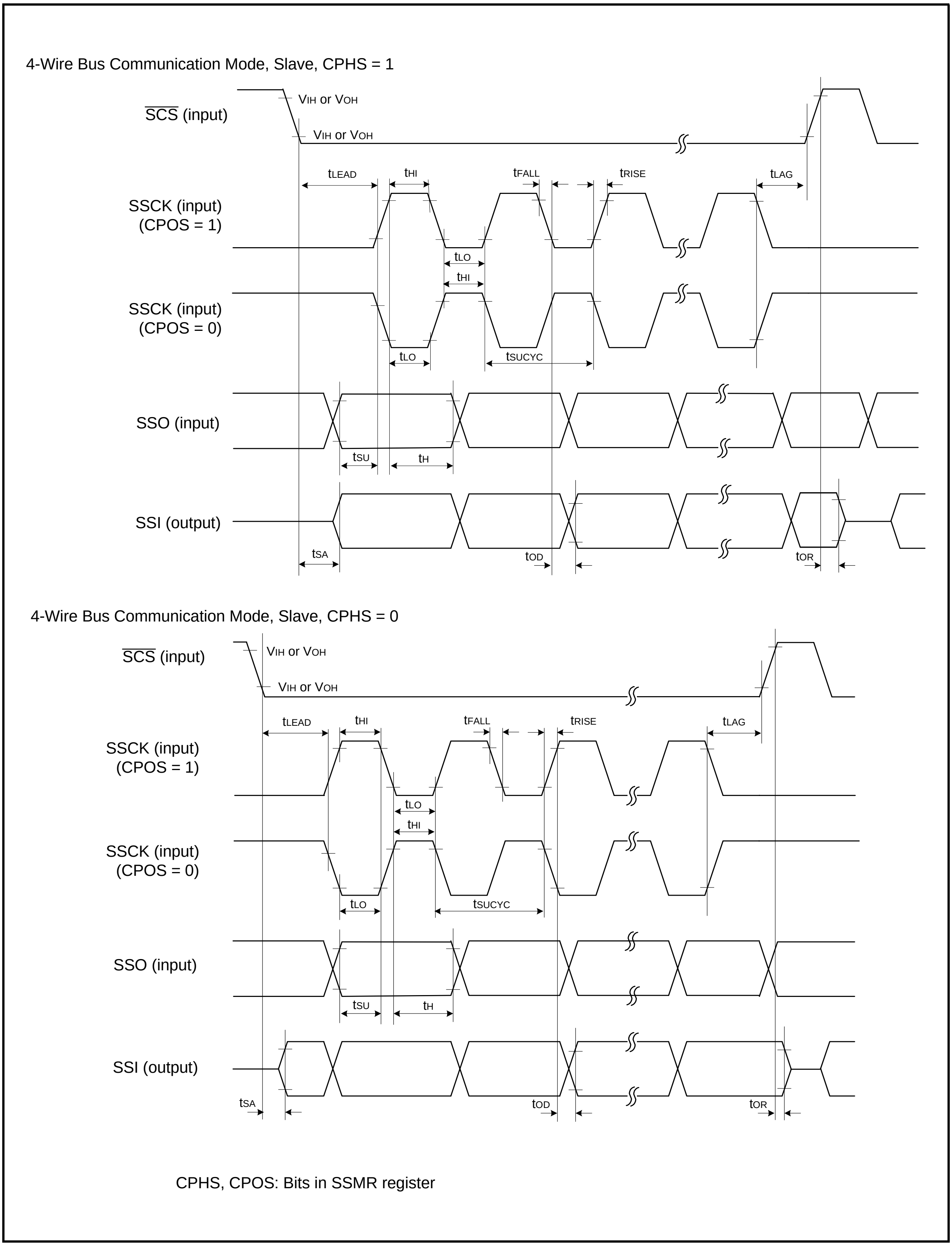
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por1}	Power-on reset valid voltage(4)		–	–	0.1	V
V_{por2}	Power-on reset or voltage monitor 1 reset valid voltage		0	–	V_{det1}	V
t_{rth}	External power V_{CC} rise gradient	$V_{CC} \leq 3.6$ V	20(2)	–	–	mV/msec
		$V_{CC} > 3.6$ V	20(2)	–	2,000	mV/msec

NOTES:
1. The measurement condition is T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. This condition (the minimum value of external power V_{CC} rise gradient) does not apply if $V_{por2} \geq 1.0$ V.
3. To use the power-on reset function, enable voltage monitor 1 reset by setting the LVD1ON bit in the OFS register to 0, the VW1C0 and VW1C6 bits in the VW1C register to 1 respectively, and the VCA26 bit in the VCA2 register to 1.
4. $t_{w(por1)}$ indicates the duration the external power V_{CC} must be held below the effective voltage (V_{por1}) to enable a power on reset. When turning on the power for the first time, maintain $t_{w(por1)}$ for 30 s or more if $-20°C \leq T_{opr} \leq 125°C$, maintain $t_{w(por1)}$ for 3,000 s or more if $-40°C \leq T_{opr} < -20°C$.



NOTES:
1. When using the voltage monitor 1 digital filter, ensure VCC is 2.0 V or higher during the sampling time.
2. The sampling clock can be selected. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.
3. V_{det1} indicates the voltage detection level of the voltage detection 1 circuit. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.

Figure 5.22 Reset Circuit Electrical Characteristics


4-Wire Bus Communication Mode, Slave, CPHS = 1

4-Wire Bus Communication Mode, Slave, CPHS = 0

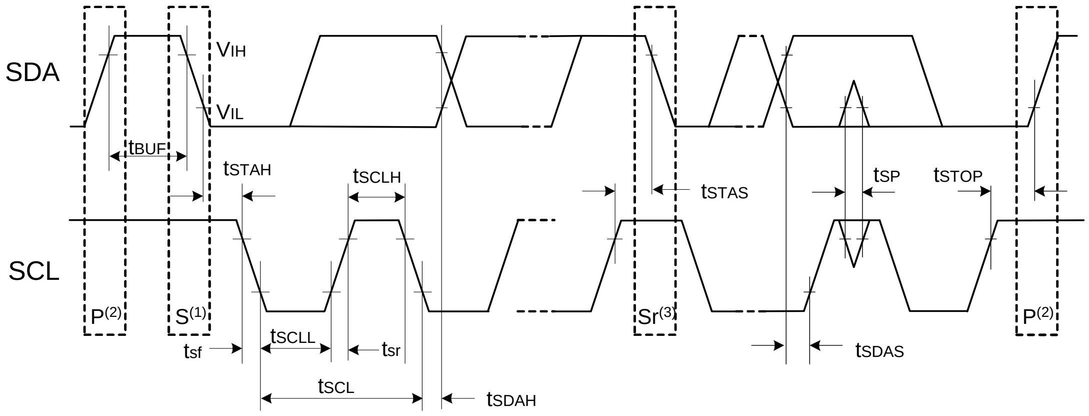
CPHS, CPOS: Bits in SSMR register

Figure 5.24 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Slave)

Table 5.46 Timing Requirements of I^{2}C bus Interface(1)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{SCL}	SCL input cycle time		12t_{CYC} + 600(2)	–	–	ns
t_{SCLH}	SCL input “H” width		3t_{CYC} + 300(2)	–	–	ns
t_{SCLL}	SCL input “L” width		5t_{CYC} + 500(2)	–	–	ns
t_{sf}	SCL, SDA input fall time		–	–	300	ns
t_{SP}	SCL, SDA input spike pulse rejection time		–	–	1t_{CYC}(2)	ns
t_{BUF}	SDA input bus-free time		5t_{CYC}(2)	–	–	ns
t_{STAH}	Start condition input hold time		3t_{CYC}(2)	–	–	ns
t_{STAS}	Retransmit start condition input setup time		3t_{CYC}(2)	–	–	ns
t_{STOP}	Stop condition input setup time		3t_{CYC}(2)	–	–	ns
t_{SDAS}	Data input setup time		1t_{CYC} + 20(2)	–	–	ns
t_{SDAH}	Data input hold time		0	–	–	ns

NOTES:
1. V_{CC} = 2.7 to 5.5 V, V_{SS} = 0 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. 1t_{CYC} = 1/f1(s)



NOTES:
1. Start condition
2. Stop condition
3. Retransmit start condition

Figure 5.26 I/O Timing of I^{2}C bus Interface

Timing Requirements
(Unless Otherwise Specified: V_{CC} = 5 V, V_{SS} = 0 V at T_{opr} = 25°C) [V_{CC} = 5 V]

Table 5.49 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	25	–	ns
$t_{WL(XIN)}$	XIN input “L” width	25	–	ns

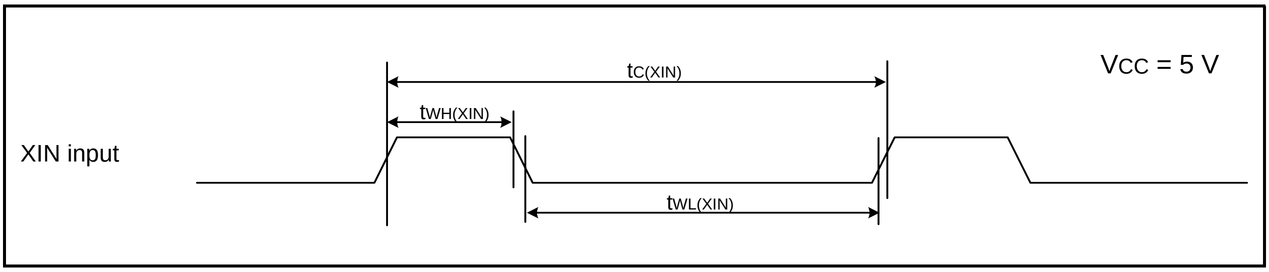


Figure 5.27 XIN Input Timing Diagram when V_{CC} = 5 V

Table 5.50 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

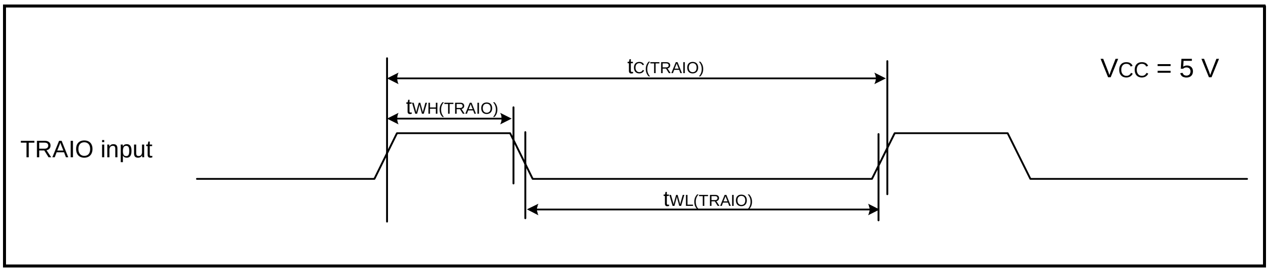


Figure 5.28 TRAIO Input Timing Diagram when V_{CC} = 5 V

Table 5.53 Electrical Characteristics (3) [V_{CC} = 3 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except XOUT	I_{OH} = -1 mA		V_{CC} - 0.5	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -0.1 mA	V_{CC} - 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -50 µA	V_{CC} - 0.5	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except XOUT	I_{OL} = 1 mA		–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, SSI, SCL, SDA, SSO			0.1	0.3	–	V
		$\overline{RESET}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V, V_{CC} = 3V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 3V		–	–	-4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 3V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		2.0	–	–	V

NOTE:

1. V_{CC} = 2.7 to 3.3 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), f(XIN) = 10 MHz, unless otherwise specified.

REVISION HISTORY

R8C/28 Group, R8C/29 Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.10	Nov 14, 2005	–	First Edition issued
0.30	Feb 28, 2006	all pages	“J, K version” added
		1	1.1 Applications revised
		2	Table 1.1 Functions and Specifications for R8C/28 Group revised
		3	Table 1.2 Functions and Specifications for R8C/29 Group revised
		4	Figure 1.1 Block Diagram; NOTE3 added
		5	Table 1.3 Product Information for R8C/28 Group and Figure 1.2 Type Number, Memory Size, and Package of R8C/28 Group revised
		6	Table 1.4 Product Information for R8C/29 Group and Figure 1.3 Type Number, Memory Size, and Package of R8C/29 Group revised
		7	Figure 1.4 Pin Assignments (Top View); NOTE3 added
		8	Table 1.5 Pin Functions revised
		9	Table 1.6 Pin Name Information by Pin Number; “XOUT” → “XOUT/XCOUT”, “XIN” → “XIN/XCIN” revised and NOTE2 added
		13	Figure 3.1 Memory Map of R8C/28 Group; “R5F21284JSP, R5F21284KSP” added
		14	Figure 3.2 Memory Map of R8C/29 Group; “R5F21294JSP, R5F21294KSP” added
		15	Table 4.1 SFR Information (1); NOTE6 added
		18	Table 4.4 SFR Information (4); 00FEh: “DRR” → “P1DRR” symbol name revised
		22 to 66	5. Electrical Characteristics added
0.40	Mar 29, 2006	2	Table 1.1 Functions and Specifications for R8C/28 Group revised
		3	Table 1.2 Functions and Specifications for R8C/29 Group revised
		15	Table 4.1 SFR Information (1); - 0032h, 0036h, 0038h revised - NOTES 2 to 6 revised and NOTES 7 to 8 added
		19	Table 4.5 SFR Information (5); NOTE2 added
0.50	Apr 27, 2006	18	Table 4.4; 00FDh: revised
		46	Table 5.35; System clock Conditions: revised
1.00	Nov 08, 2006	All pages	“PRELIMINARY” deleted
		1	1 “J and K versions are under development...notice.” added
		2	Table 1.1 revised
		3	Table 1.2 revised
		4	Figure 1.1 revised
		5	Table 1.3 revised
		6	Table 1.4 revised